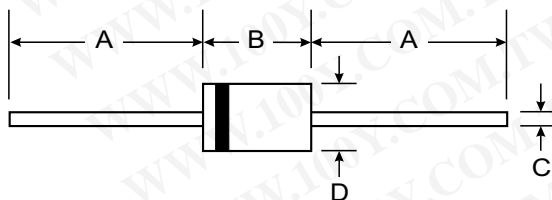


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150mA Axial Leaded Fast Switching Diode

Features

- Fast Switching Speed
- General Purpose Rectification
- Silicon Epitaxial Planar Construction



Mechanical Data

- Case: DO-35
- Leads: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Marking: Type Number
- Weight: 0.13 grams (approx.)

DO-35		
Dim	Min	Max
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics

@ T_A = 25°C unless otherwise specified

Characteristic	Symbol	1N4148	1N4448	Unit	
Non-Repetitive Peak Reverse Voltage	V _{RM}	100		V	
Peak Repetitive Reverse Voltage	V _{RRM}	75		V	
Working Peak Reverse Voltage	V _{RWM}	75		V	
DC Blocking Voltage	V _R	75		V	
RMS Reverse Voltage	V _{R(RMS)}	53		V	
Forward Continuous Current (Note 1)	I _{FM}	300	500	mA	
Average Rectified Output Current (Note 1)	I _O	150		mA	
Non-Repetitive Peak Forward Surge Current @ t = 1.0s @ t = 1.0μs	I _{FSM}	1.0 2.0		A	
Power Dissipation (Note 1) Derate Above 25°C	P _d	500 1.68		mW mW/°C	
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	300		K/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +175		°C	
Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage	V _{FM}	0.62	1.0	V	I _F = 10mA I _F = 5.0mA I _F = 100mA
Maximum Peak Reverse Current	I _{RM}	—	5.0 50 30 25	μA μA μA nA	V _R = 75V V _R = 70V, T _J = 150°C V _R = 20V, T _J = 150°C V _R = 20V
Capacitance	C _j	—	4.0	pF	V _R = 0, f = 1.0MHz
Reverse Recovery Time	t _{rr}	—	4.0	ns	I _F = 10mA to I _R = 1.0mA V _R = 6.0V, R _L = 100Ω

Notes: 1. Valid provided that device terminals are kept at ambient temperature.

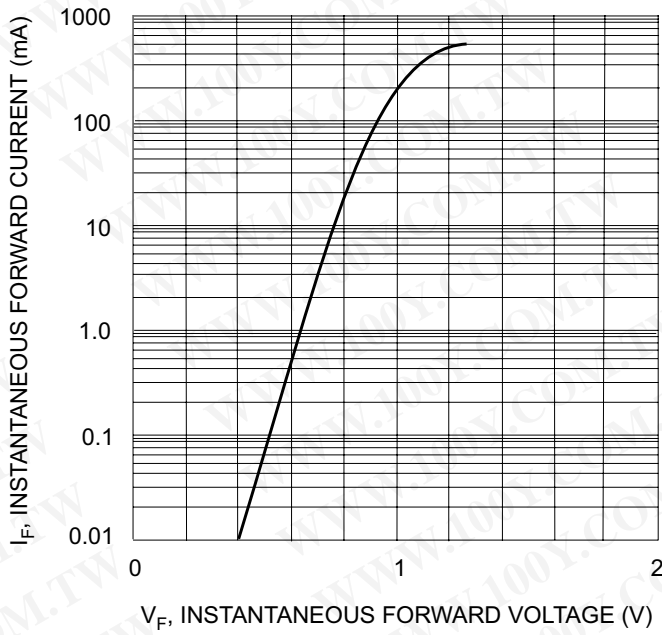


Fig. 1 Forward Characteristics

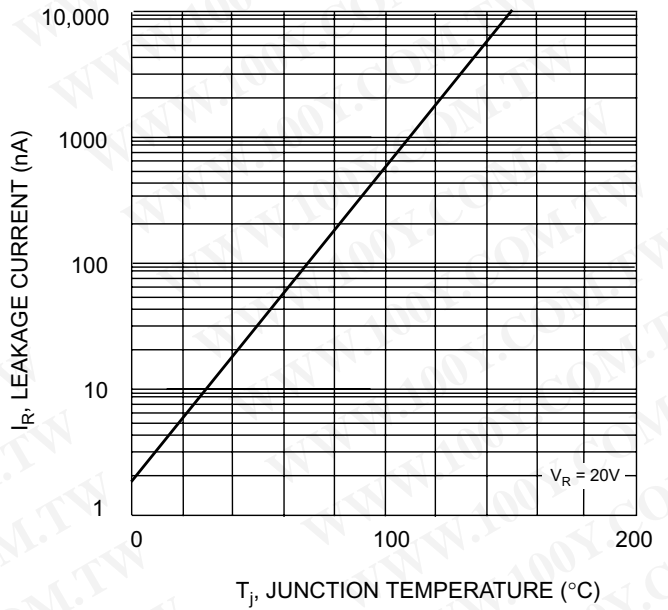


Fig. 2, Leakage Current vs Junction Temperature